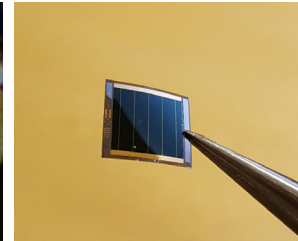
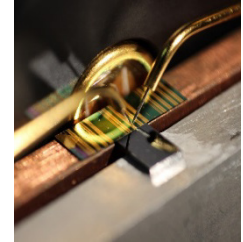
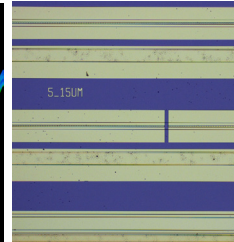
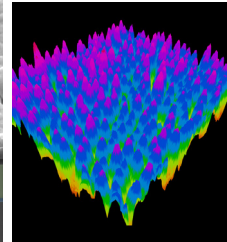
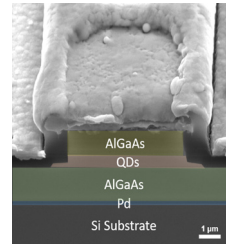


- RIT recently completed installation of a new Aixtron Close Coupled Showerhead (CCS) MOCVD
  - 3x2", 1x3" and 1x4" capability
  - **Epitaxy of III-V compounds of As, P and Sb**
  - In-situ diagnostic LayTec EpiTT-Curve system gives real time information of temperature, stress, strain and surface roughness
  - Materials used for advanced applications in solar energy, integrated photonics, nanomanufacturing, infrared detectors and next generation electronics





- Staff of the RIT Epitaxy Facility are available to work with customers for any standard or customized growth or device structure.
- All growth runs are completed in-house by our staff of research scientists, all of whom have advanced training in semiconductors and epitaxy.
- Base cost for tool use is the per-run cost to use the tool, but does not include precursor material costs.
- Any additional time for design or product development is not included and would be a separate charge.
- Commercial rates need to be adjusted to account for personnel costs

## Source/ Material Costs

Source/ Material Costs are based on the actual cost of materials consumed. Calculations for this cost is project specific, depending on substrate and growth requirements.

Current Options:

Wafers : GaAs, InP, GaSb (test and prime wafers)

Metal Oxide: TMAI/ TEGa/ TMGa/ TTBAI/ DEZn/ TMIn/ TBAs/ TMSb

Hydrides: AsH<sub>3</sub> / PH<sub>3</sub>

2018 Base Rate for MOCVD		
Rates effective Oct 1, 2017-Sept 30, 2018		
	Federal Rates RIT and other University customers	Commercial Rates all others
Base Cost/ Run	\$140	Based on customer needs
for runs < 2:30; +\$20 for each additional 15 min.		Quotes available upon request
The Base Cost is applied to all MOVPE growths and is a per run charge. Projects are invoiced monthly/		